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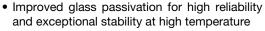
Vishay Semiconductors

Medium Power Phase Control Thyristors (Stud Version), 25 A



| PRODUCT SUMMARY | | | | |
|------------------------------------|------------------|--|--|--|
| Package | TO-208AA (TO-48) | | | |
| Diode variation | Single SCR | | | |
| I _{T(AV)} | 25 A | | | |
| V _{DRM} /V _{RRM} | 100 V to 1200 V | | | |
| V _{TM} | 1.70 V | | | |
| I _{GT} | 60 mA | | | |
| TJ | -65 °C to 125 °C | | | |

FEATURES





- High dl/dt and dV/dt capabilities
- Standard package
- · Low thermal resistance
- · Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- Designed and qualified for industrial and consumer level
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- Medium power switching
- Phase control applications
- Can be supplied to meet stringent military, aerospace and other high reliability requirements

| MAJOR RATINGS AND CHARACTERISTICS | | | | | |
|------------------------------------|-----------------|-------------|------------------|--|--|
| PARAMETER | TEST CONDITIONS | VALUES | UNITS | | |
| 1 | | 25 | А | | |
| I _{T(AV)} | T _C | 85 | °C | | |
| I _{T(RMS)} | | 40 | A | | |
| I _{TSM} | 50 Hz | 420 | A | | |
| | 60 Hz | 440 | | | |
| 10. | 50 Hz | 867 | A ² s | | |
| I ² t | 60 Hz | 790 | | | |
| V _{DRM} /V _{RRM} | | 100 to 1200 | V | | |
| tq | Typical | 110 | μs | | |
| T _J | | -65 to 125 | °C | | |

ELECTRICAL SPECIFICATIONS

| VOLTAGE RATINGS | | | | | | | |
|-----------------|-----------------|---|---|---|--|--|--|
| TYPE NUMBER | VOLTAGE CODE | V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V | V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V | $\begin{aligned} &I_{DRM}/I_{RRM} \text{ MAXIMUM} \\ &AT T_J = T_J \text{ MAXIMUM} \\ & \text{mA} \end{aligned}$ | | | |
| | 10 | 100 | 150 | 20 | | | |
| | 20 | 200 | 300 | | | | |
| | 40 | 400 | 500 | | | | |
| VS-25RIA | 60 | 600 | 700 | 10 | | | |
| | 80 | 800 | 900 | 10 | | | |
| | 100 | 1000 | 1100 | | | | |
| | 120 | 1200 | 1300 | | | | |

Notes

⁽¹⁾ Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

 $[\]ensuremath{^{(2)}}$ For voltage pulses with $t_p \leq 5 \ ms$



| ABSOLUTE MAXIMUM RAT | | İ | TEST OCHE | NTIONS | VALUEC | LINUTO |
|---|---------------------|--|--|----------------------------------|--------|------------------|
| PARAMETER | SYMBOL | | TEST CONE | DITIONS | VALUES | UNITS |
| Maximum average on-state current | I _{T(AV)} | 180° sinusoi | 180° sinusoidal conduction | | 25 | Α |
| at case temperature | · I (AV) | 100 0111001 | dai conduction | | 85 | °C |
| Maximum RMS on-state current | I _{T(RMS)} | | | | 40 | А |
| | | t = 10 ms | No voltage | | 420 | |
| Maximum peak, one-cycle | | t = 8.3 ms | reapplied | | 440 | _ |
| non-repetitive surge current | I _{TSM} | t = 10 ms | 100 % V _{RRM} | | 350 | Α |
| | reapplied | Sinusoidal half wave, | 370 | | | |
| Maximum I ² t for fusing | | t = 10 ms | No voltage | I RRM | 867 | A ² s |
| | l ² t | t = 8.3 ms | reapplied | | 790 | |
| | | t = 10 ms | 100 % V _{RRM} reapplied | | 615 | |
| | | t = 8.3 ms | | | 560 | |
| Maximum I ² √t for fusing | I²√t | t = 0.1 to 10 ms, no voltage reapplied, $T_J = T_J$ maximum | | 8670 | A²√s | |
| Low level value of threshold voltage | V _{T(TO)1} | (16.7 % x π | $x \mid_{T(AV)} < I < \pi x \mid$ | $T_{(AV)}$, $T_J = T_J$ maximum | 0.99 | V |
| High level value of threshold voltage | V _{T(TO)2} | $(I > \pi \times I_{T(AV)})$ | , T _J = T _J maximu | ım | 1.40 | v |
| Low level value of on-state slope resistance | r _{t1} | (16.7 % x π : | (16.7 % x π x I _{T(AV)} < I < π x I _{T(AV)}), T _J = T _J maximum | | 10.1 | 0 |
| High level value of on-state slope resistance | r _{t2} | $(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$ | | 5.7 | mΩ | |
| Maximum on-state voltage | V _{TM} | I _{pk} = 79 A, T _J = 25 °C | | | 1.70 | V |
| Maximum holding current | I _H | T 05.00 a | | | 130 | |
| Latching current | IL | T _J = 25 °C, anode supply 6 V, resistive load | | 200 | - mA | |

| SWITCHING | | | | | |
|-------------------------------|------------------------------|-----------------|---|--------|-------|
| PARAMETER | | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| | $V_{DRM} \le 600 \text{ V}$ | | $T_J = T_J$ maximum, $V_{DM} = Rated V_{DRM}$ dI/dt Gate pulse = 20 V, 15 Ω, $t_p = 6$ μs, $t_r = 0.1$ μs maximum – $I_{TM} = (2 \text{ x rated dI/dt}) A$ | 200 | A/μs |
| Maximum rate of rise | $V_{DRM} \le 800 \text{ V}$ | d1/d+ | | 180 | |
| of turned-on current | $V_{DRM} \le 1000 \text{ V}$ | di/dt | | 160 | |
| V _{DRM} ≤ 1600 ° | | | ,, | 150 | |
| Typical turn-on time | | t _{gt} | $T_J = 25$ °C, at rated V_{DRM}/V_{RRM} , $T_J = 125$ °C | 0.9 | |
| Typical reverse recovery time | | t _{rr} | $T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$, $t_p > 200 \ \mu s$, $dI/dt = -10 \ A/\mu s$ | 4 | μs |
| Typical turn-off time | | t _q | $\begin{split} T_J = T_J &\text{ maximum, } I_{TM} = I_{T(AV)}, t_p > 200 \; \mu\text{s, } V_R = 100 \; V, \\ dI/dt = - 10 \; A/\mu\text{s, } dV/dt = 20 \; V/\mu\text{s linear to 67 } \% \; V_{DRM}, \\ gate &\text{ bias 0 V to 100 W} \end{split}$ | 110 | μο |

Note

• $t_q = 10 \mu s$ up to 600 V, $t_q = 30 \mu s$ up to 1600 V available on special request

| BLOCKING | | | | |
|-------------------------------|--------|--|---------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS |
| Maximum critical rate of rise | dV/dt | T _J = T _J maximum linear to 100 % rated V _{DRM} | 100 | V/µs |
| of off-state voltage | av/at | T _J = T _J maximum linear to 67 % rated V _{DRM} | 300 (1) | ν/μδ |

Note

⁽¹⁾ Available with: $dV/dt = 1000 V/\mu s$, to complete code add S90 i.e. 25RIA120S90



| TRIGGERING | | | | | |
|-------------------------------------|--------------------|---|---|--------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | VALUES | UNITS |
| Maximum peak gate power | P _{GM} | T T | | 8.0 | W |
| Maximum average gate power | P _{G(AV)} | - IJ = IJ Maximum | $T_J = T_J$ maximum | | |
| Maximum peak positive gate current | I _{GM} | $T_J = T_J$ maximum | | 1.5 | Α |
| Maximum peak negative gate voltage | -V _{GM} | $T_J = T_J$ maximum | | 10 | V |
| | | T _J = - 65 °C | | 90 | |
| DC gate current required to trigger | I _{GT} | T _J = 25 °C | Maximum required gate trigger current/voltage are the lowest value which will trigger all units | 60 | mA |
| | | T _J = 125 °C | | 35 | |
| | V _{GT} | T _J = - 65 °C | | 3.0 | V |
| DC gate voltage required to trigger | | T _J = 25 °C | 6 V anode to cathode applied | 2.0 | |
| | | T _J = 125 °C | | 1.0 | |
| DC gate current not to trigger | I _{GD} | $T_J = T_J$ maximum, V_E | _{DRM} = Rated value | 2.0 | mA |
| DC gate voltage not to trigger | V_{GD} | $T_J = T_J$ maximum, $V_{DRM} = Rated value$ | Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied | 0.2 | V |

| THERMAL AND MECHANICAL SPECIFICATIONS | | | | | |
|--|-----------------------------------|--|---------------------|------------|--|
| PARAMETER | SYMBOL | TEST CONDITIONS | VALUES | UNITS | |
| Maximum operating junction and storage temperature range | T _J , T _{Stg} | | - 65 to 125 | °C | |
| Maximum thermal resistance, junction to case | R _{thJC} | DC operation | 0.75 | K/W | |
| Maximum thermal resistance, case to heatsink | R _{thCS} | Mounting surface, smooth, flat and greased | | r\/ VV | |
| Allowable mounting torque | | Non-lubricated threads | 3.4 + 0 - 10 % (30) | N⋅m | |
| Allowable mounting torque | | Lubricated threads | 23 + 0 - 10 % (20) | (lbf · in) | |
| Approximate weight | | | 14 | g | |
| Approximate weight | | | 0.49 | OZ. | |
| Case style | | See dimensions - link at the end of datasheet TO-208AA (TO-4 | | (TO-48) | |

| △R _{thJC} CONDUCTION | | | | |
|-------------------------------|-----------------------|------------------------|---------------------|-------|
| CONDUCTION ANGLE | SINUSOIDAL CONDUCTION | RECTANGULAR CONDUCTION | TEST CONDITIONS | UNITS |
| 180° | 0.17 | 0.13 | | |
| 120° | 0.21 | 0.22 | | |
| 90° | 0.27 | 0.30 | $T_J = T_J$ maximum | K/W |
| 60° | 0.40 | 0.42 | | |
| 30° | 0.69 | 0.70 | | |

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

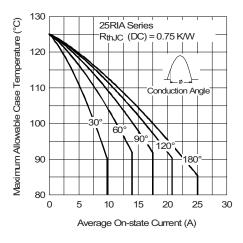


Fig. 1 - Current Ratings Characteristics

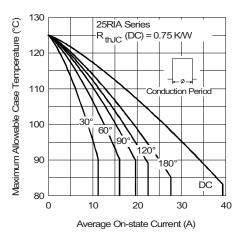


Fig. 1 - Current Ratings Characteristics

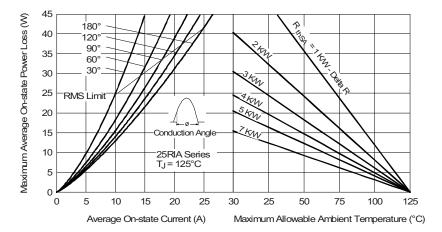


Fig. 2 - On-State Power Loss Characteristics

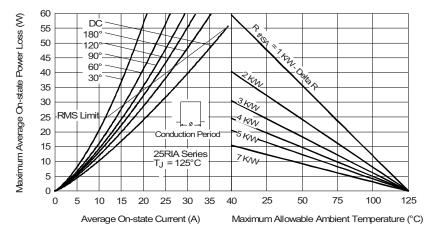


Fig. 3 - On-State Power Loss Characteristics



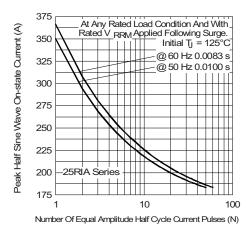


Fig. 4 - Maximum Non-Repetitive Surge Current

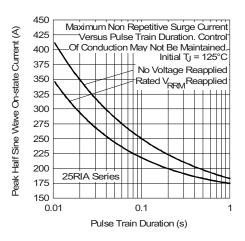


Fig. 5 - Maximum Non-Repetitive Surge Current

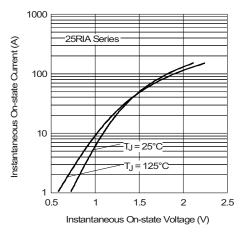


Fig. 6 - Forward Voltage Drop Characteristics

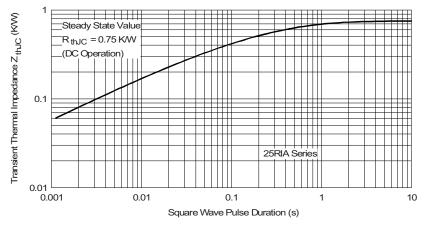


Fig. 7 - Thermal Impedance Z_{thJC} Characteristics



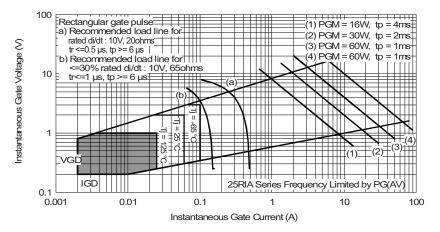
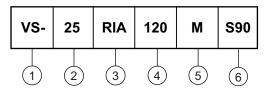


Fig. 8 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current code

3 - Essential part number

Voltage code x 10 = V_{RRM} (see Voltage Ratings table)

None = Stud base TO-208AA (TO-48) 1/4" 28UNF-2A
 M = Stud base TO-208AA (TO-48) M6 x 1

6 - Critical dV/dt:

None = 300 V/µs (standard value)

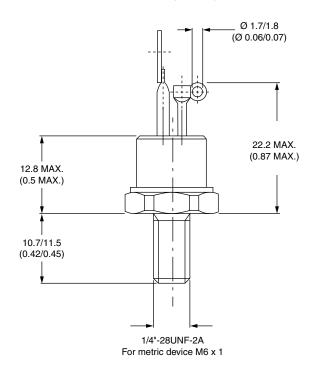
S90 = 1000 V/µs (special selection)

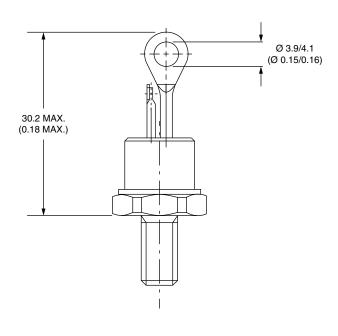
| LINKS TO RELAT | TED DOCUMENTS |
|----------------|--------------------------|
| Dimensions | www.vishay.com/doc?95333 |

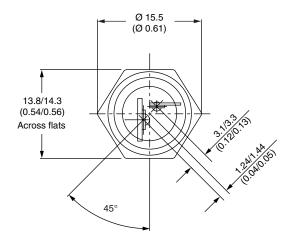


TO-208AA (TO-48)

DIMENSIONS in millimeters (inches)









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Authorized Distribution Brand:

























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